

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
60V	9.5mΩ @ V _{GS} = 10V	45A
	13.3mΩ @ V _{GS} = 4.5V	36A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management Functions
- DC-DC Converters
- Synchronous Rectifier

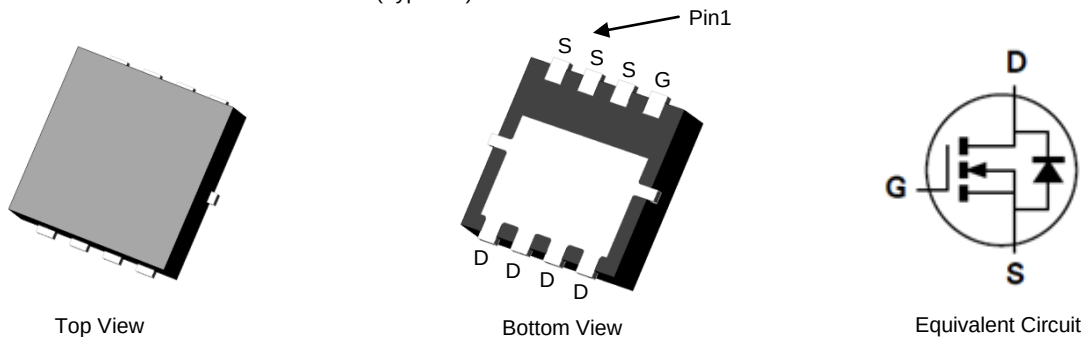
Features

- 100% Unclamped Inductive Switching – Ensures more reliable and robust end application
- Low On-Resistance
- Low Input Capacitance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: PowerDI[®] 3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (Type UX)

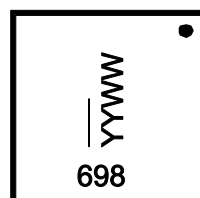


Ordering Information (Note 4)

Part Number	Case	Packaging
DMT69M8LFV-7	PowerDI3333-8 (Type UX)	2000/Tape & Reel
DMT69M8LFV-13	PowerDI3333-8 (Type UX)	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



698 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±16	V
Continuous Drain Current (Note 5) V _{GS} = 10V	T _C = +25°C	I _D	45	A
	T _C = +70°C	I _D	37	A
	T _A = +25°C	I _D	11	A
	T _A = +70°C	I _D	8.9	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	60	A
Maximum Continuous Body Diode Forward Current (Note 5)		I _S	2	A
Avalanche Current, L = 0.1mH		I _{AS}	20.3	A
Avalanche Energy, L = 0.1mH		E _{AS}	20.6	mJ
V _{DS} Spike	t = 10μs	V _{SPIKE}	72	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	57	°C/W
Total Power Dissipation (Note 5)	T _C = +25°C	P _D	42	W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	3	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	7.5	9.5	mΩ	V _{GS} = 10V, I _D = 13.5A
		—	9.9	13.3		V _{GS} = 4.5V, I _D = 11.5A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 13.5A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	1925	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	438	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	41	—	pF	
Gate Resistance	R _g	—	1.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	33.5	—	nC	V _{DS} = 30V, I _D = 13.5A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	15.6	—	nC	
Gate-Source Charge	Q _{gs}	—	4.7	—	nC	
Gate-Drain Charge	Q _{gd}	—	5.3	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.5	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 6Ω, I _D = 13.5A
Turn-On Rise Time	t _R	—	8.6	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	35.9	—	ns	
Turn-Off Fall Time	t _F	—	15.7	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	18.2	—	ns	I _F = 13.5A, di/dt = 400A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	33.1	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

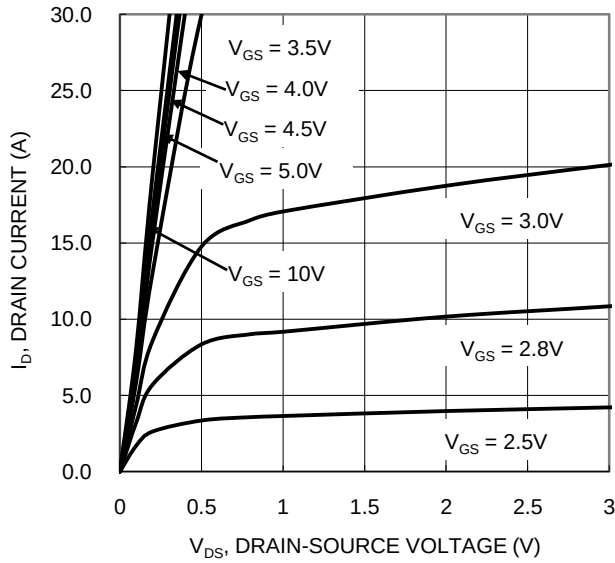


Figure 1. Typical Output Characteristic

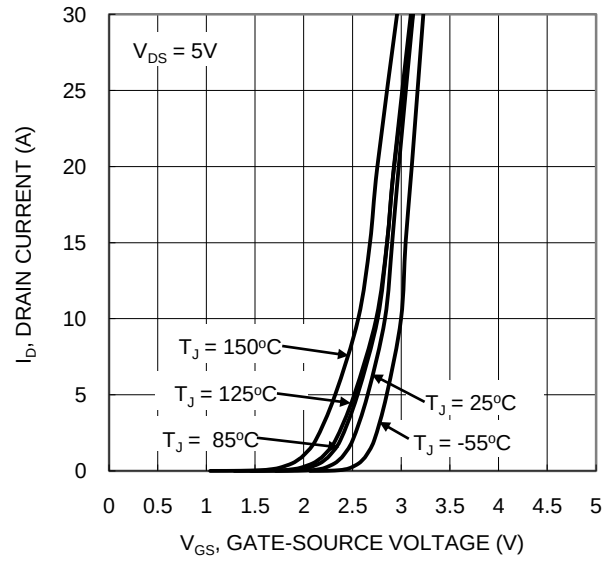


Figure 2. Typical Transfer Characteristic

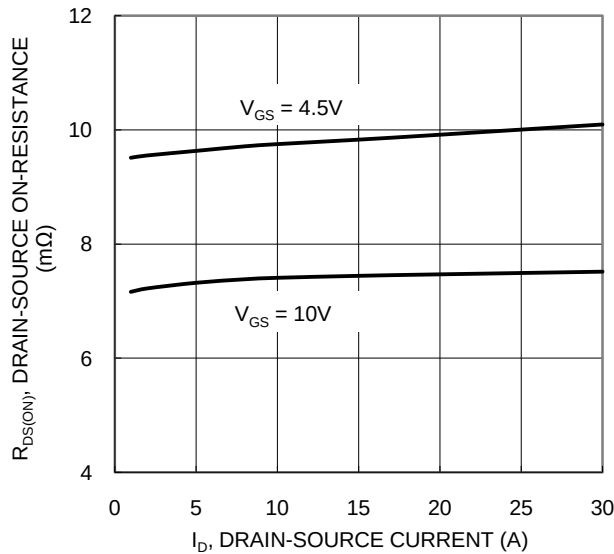


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

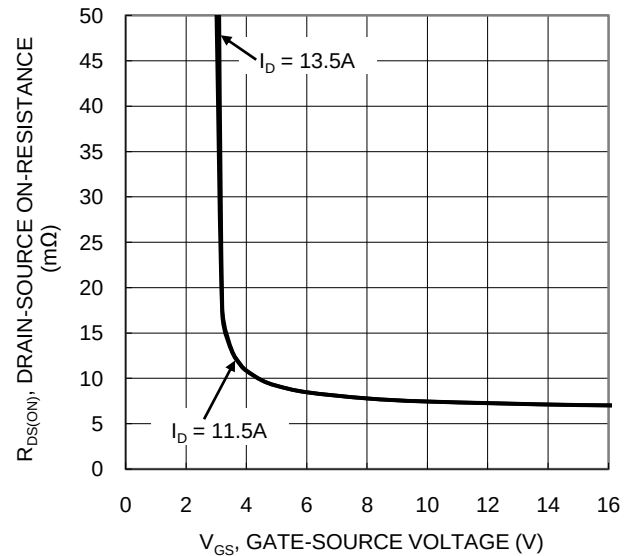


Figure 4. Typical Transfer Characteristic

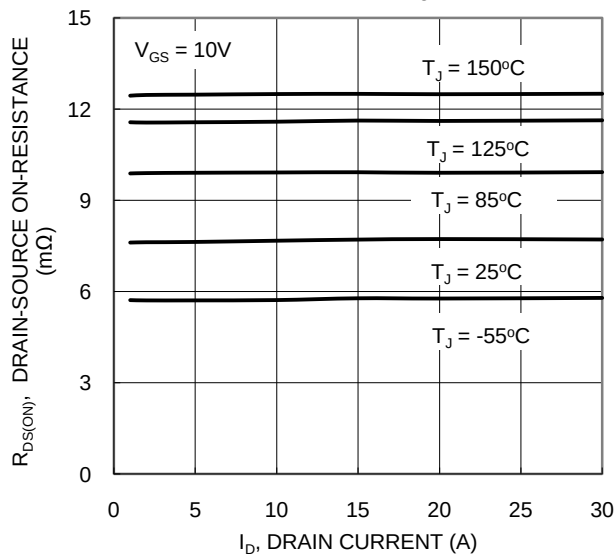


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

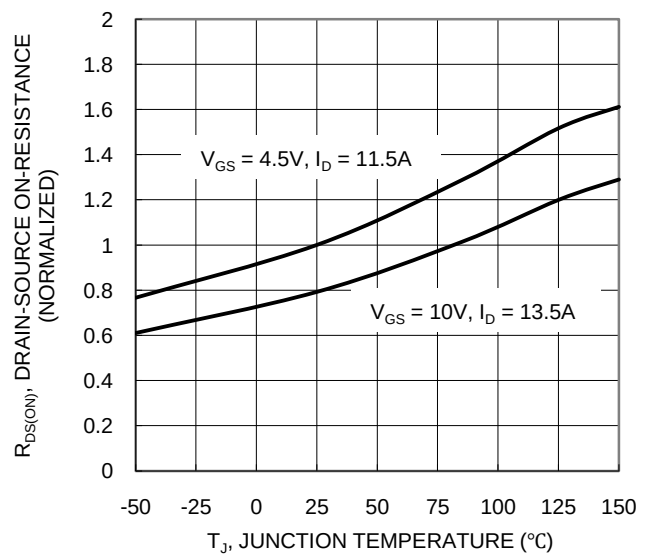


Figure 6. On-Resistance Variation with Junction Temperature

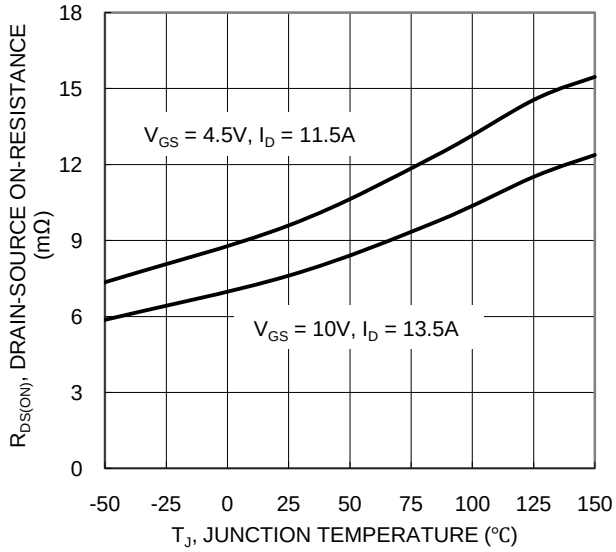


Figure 7. On-Resistance Variation with Junction Temperature

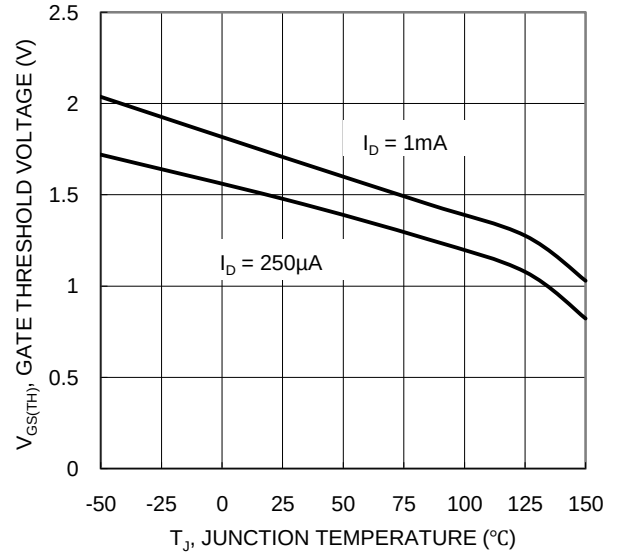


Figure 8. Gate Threshold Variation vs. Junction Temperature

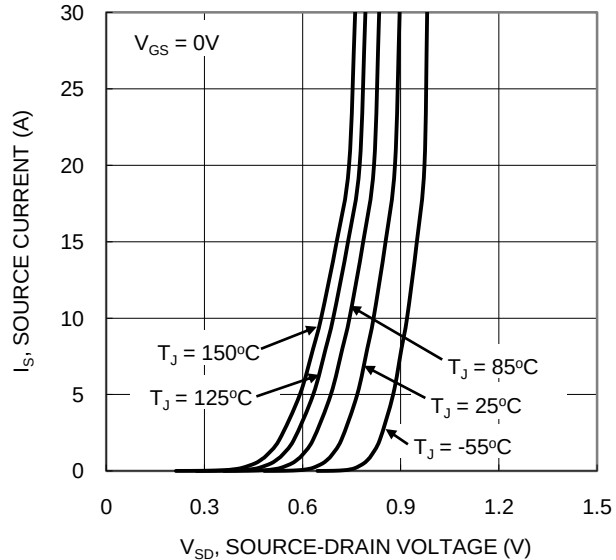


Figure 9. Diode Forward Voltage vs. Current

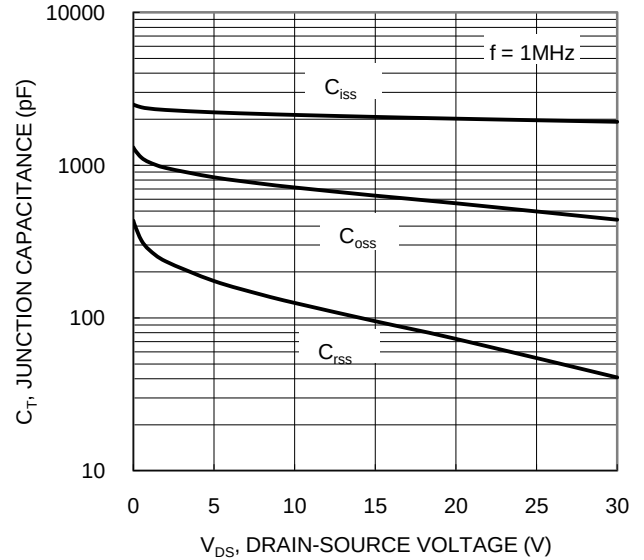


Figure 10. Typical Junction Capacitance

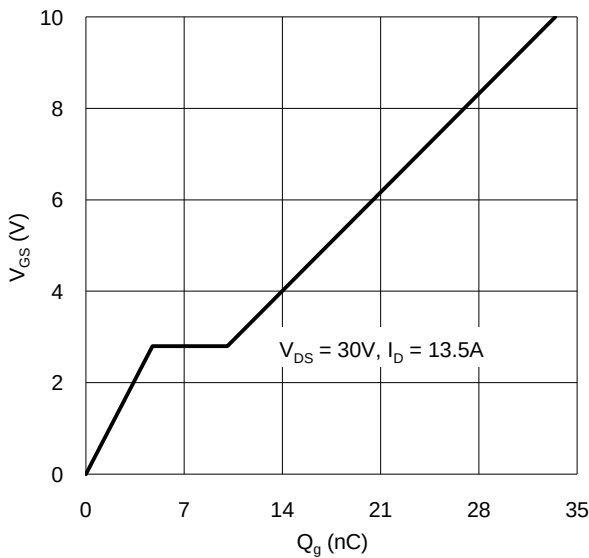


Figure 11. Gate Charge

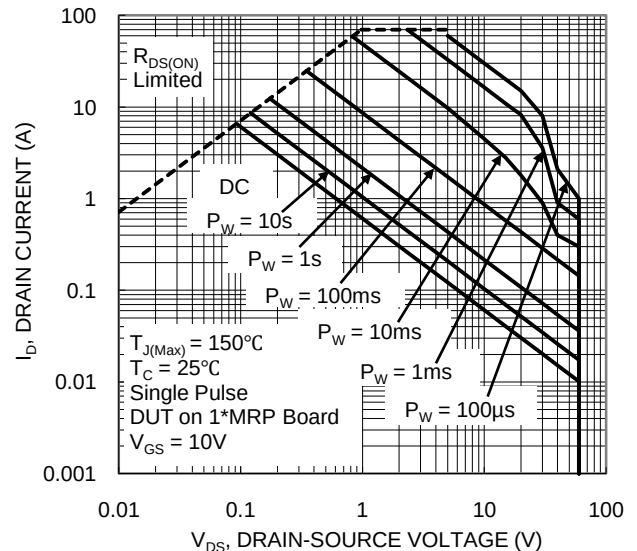


Figure 12. SOA, Safe Operation Area

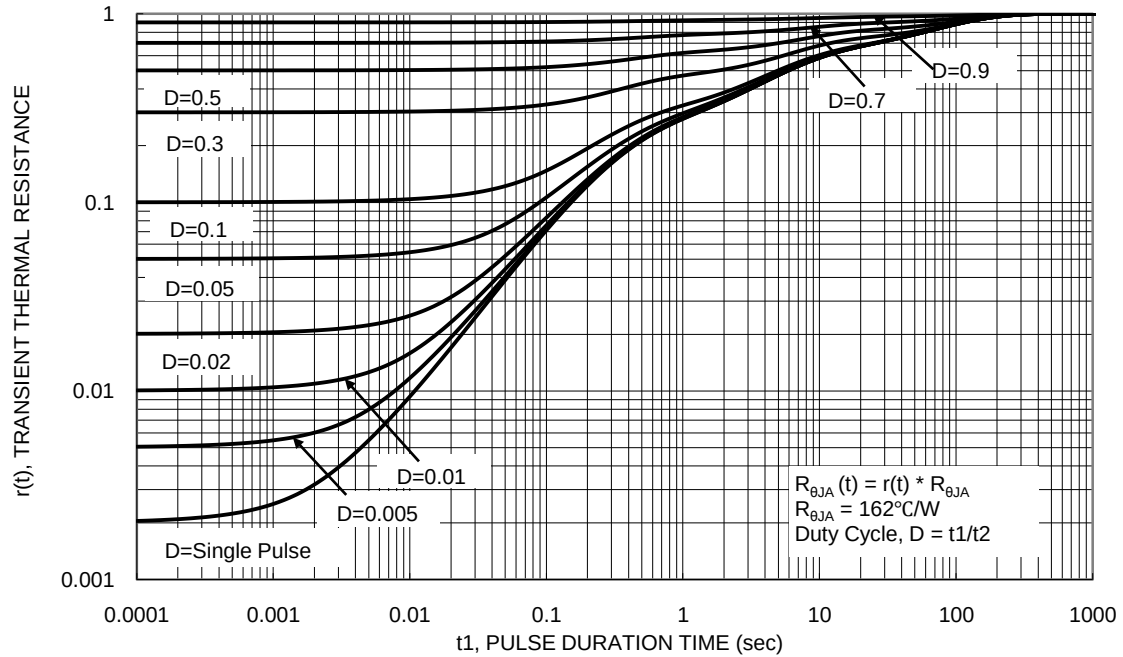
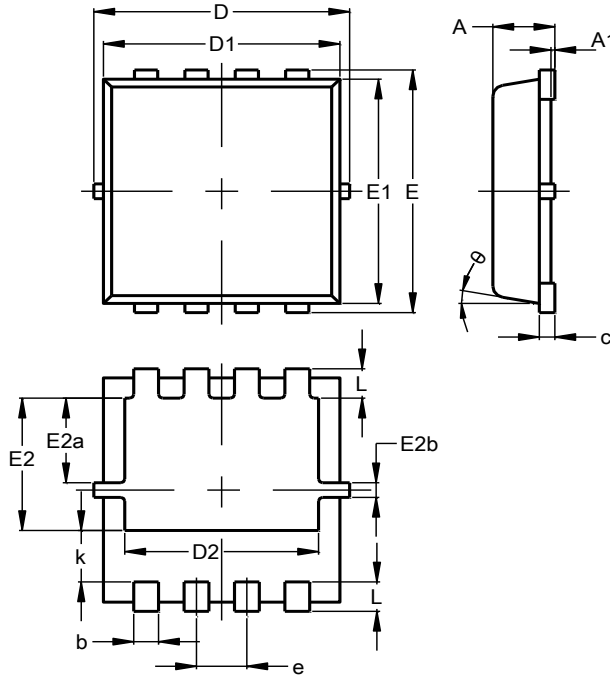


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (Type UX)

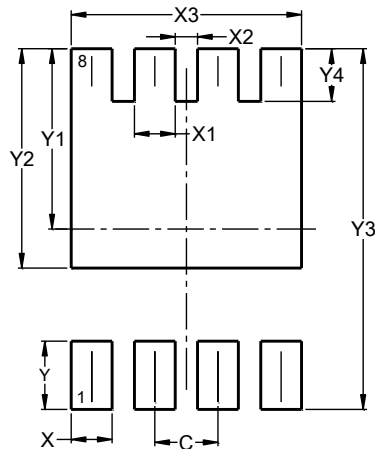


PowerDI3333-8 (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E2a	0.95	1.35	1.15
E2b	0.10	0.30	0.20
e	0.65 BSC		
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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